

37 CFR 1.501  
**INFORMATION DISCLOSURE STATEMENT  
 IN A PATENT**  
 (use several sheets if necessary)



Docket No.  
 113278-005

Serial No.  
 10/062,687

Applicant:  
 Okuyama et al.

Filing Date  
 Jan. 30, 2002

Group Art Unit  
 2813

### U.S. PATENT DOCUMENTS

Examiner's Initials		Document Number	Date	Name	Class	Subclas s	Filing Date If appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

### FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclas s	Translation	
							Yes	No
<i>[Signature]</i>	AL	6-45648	2-18-94	Japan				
<i>[Signature]</i>	AM	9-129974	5-16-97	Japan				
<i>[Signature]</i>	AN	11-26883	1-29-99	Japan				
	AO							
	AP							
	AQ							
	AR							
	AS							

### OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>[Signature]</i>	AT	Applied Physics Letters, Vol. 76, Number 22, 29 May 2000, "Selective growth at InGaN quantum dot structures and their microphotoluminescence at room temperature, Tachibani et al., pages 3212-3214
<i>[Signature]</i>		Journal of Crystal Growth 189/190 (1998) 83-86, "Spatial control of InGaN luminescence by MOCVD selective epitaxy", Kaplnek et al.
<i>[Signature]</i>		Journal of Crystal Growth, Volume 204, No. 3, pp. 247-418 July 11 (1999), Stringfellow, et al.

Examiner

Date Considered

1/15/04

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

# 2

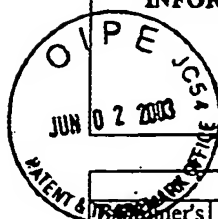
<b>INFORMATION DISCLOSURE STATEMENT</b> <b>IN AN APPLICATION</b> (Use several sheets if necessary) PTO Form 1449	Atty Docket No. 113278-005	Application No. 10/062,687
	Applicant Hiroyuki Okuyama, et al.	
	Filing Date 1/30/02	Group Unknown 2813

Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate
JMS	5,981,977	11/09/99	Furukawa et al.	—	—	

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Examiner's Initials	Document Number	Publication Date	Country	Class	Subclass	Translation	
						Yes	No
JMS	08-255929	10/01/96	Japan	—	—		
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JMS	10-265297	10/06/98	Japan	—	—		
JMS	10-270801	10/09/98	Japan	—	—		
JMS	10-312971	11/24/98	Japan	—	—		
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JMS	11-274568	10/08/99	Japan	—	—		
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JMS	J. Wang et al., Fabrication of nanoscale structures of InGaN by MOCVD lateral overgrowth, Journal of Crystal Growth 197 (1999), pp. 48-53.
JMS	Raj Singh et al., Selective Area Growth of GaN Directly on (0001) Sapphire by the HVPE Technique, MRS Internet Journal Nitride Semiconductor Research, 3, 13 (1998), pp. 1-4.
JMS	Zhigang Mao, et al., Defects in GaN Pyramids Grown on Si(111) Substrates by Selective Lateral Overgrowth, pp. 1-6; Materials Research Society Meeting in Boston, Mass. (1998).

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INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION

(Use several sheets if necessary)

PTO Form 1449

Atty Docket No.

112857-382

Application No.

10/062,687

Applicant

Okuyama, et al.

Filing Date

January 30, 2002

Group

2811 2813

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Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate

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						Yes	No
<i>[Signature]</i>	63-188938	08-04-88	Japan				
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<i>[Signature]</i>	Zheleva et al., <i>Pendeo-epitaxy - a new approach for lateral growth of gallium nitride structures</i> , MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999).
<i>[Signature]</i>	Kapolnek et al., <i>Spatial control of InGaN luminescence by MOCVD selective epitaxy</i> , Journal of Crystal Growth, 189/190 (1998) pp. 83-86.

Examiner:

*[Signature]*

Date Considered:

4/15/04

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Atty Docket No. 112857-382	Application No. 10/062,687
Applicant Okuyama et al.	
Filing Date January 30, 2002	Group <del>Unknown</del> 2813

**U.S. PATENT DOCUMENTS**

Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate
<i>[Signature]</i>	5,177,405	01-05-93	Kusuda et al.			
<i>[Signature]</i>	5,981,977	11-09-99	Furukawa et al.			

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<i>[Signature]</i>	06-067044 ✓	03-11-94	Japan				
<i>[Signature]</i>	6-45648 ✓	02-18-94	Japan				
<i>[Signature]</i>	07-199829 ✓	04-08-95	Japan				
<i>[Signature]</i>	9-129974 ✓	05-16-97	Japan				
<i>[Signature]</i>	WO 97/44612 ✓	11-27-97	PCT				
<i>[Signature]</i>	11-26883 ✓	01-29-99	Japan				
<i>[Signature]</i>	11-075019 ✓	03-16-99	Japan				
<i>[Signature]</i>	11-177138 ✓	07-02-99	Japan				
<i>[Signature]</i>	11-514136 ✓	11-30-99	Japan				
<i>[Signature]</i>	11-346004 ✓	12-14-99	Japan				

Examiner: <i>[Signature]</i>	Date Considered: 1/15/04
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